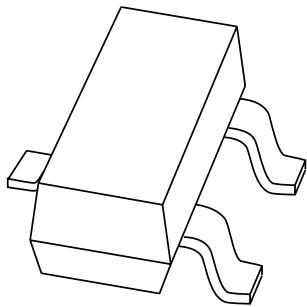


DATA SHEET



PMBF107

N-channel enhancement mode
vertical D-MOS transistor

Product specification
Supersedes data of April 1995
File under Discrete Semiconductors, SC13b

1998 Mar 06

N-channel enhancement mode vertical
D-MOS transistor

PMBF107

FEATURES

- Direct interface to C-MOS, TTL, etc.
- High-speed switching
- No secondary breakdown.

APPLICATIONS

- Relay, high-speed and line transformer drivers.

DESCRIPTION

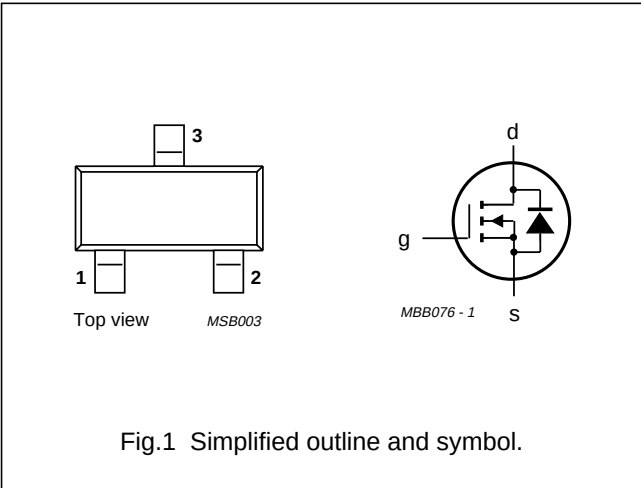
N-channel enhancement mode vertical D-MOS transistor in a SOT23 package, intended for use as a line current interruptor in telephone sets.

CAUTION

This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling. For further information, refer to Philips specs.: SNW-EQ-608, SNW-FQ-302A and SNW-FQ-302B.

PINNING - SOT23

PIN	SYMBOL	DESCRIPTION
1	g	gate
2	s	source
3	d	drain



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_{DS}	drain-source voltage		200	V
I_D	drain current (DC)		100	mA
R_{DSon}	drain-source on-resistance	$I_D = 20\text{ mA}; V_{GS} = 2.6\text{ V}$	28	Ω
V_{GSth}	gate-source threshold voltage	$I_D = 1\text{ mA}; V_{GS} = V_{DS}$	2.4	V

N-channel enhancement mode vertical D-MOS transistor

PMBF107

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{DS}	drain-source voltage		–	200	V
V_{GSO}	gate-source voltage	open drain	–	± 20	V
I_D	drain current (DC)		–	100	mA
I_{DM}	drain current	peak value	–	250	mA
P_{tot}	total power dissipation	$T_{amb} = 25\text{ }^{\circ}\text{C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$
T_j	junction temperature		–	150	$^{\circ}\text{C}$

Note

1. Device mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient; note 1	500	K/W

Note

1. Device mounted on an FR4 printed-circuit board.

CHARACTERISTICS

$T_j = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0$; $I_D = 10\text{ }\mu\text{A}$	200	–	–	V
I_{DSS}	drain-source leakage current	$V_{GS} = 0$; $V_{DS} = 130\text{ V}$	–	–	30	nA
I_{DSX}	drain cut-off current	$V_{GS} = 0.2\text{ V}$; $V_{DS} = 70\text{ V}$	–	–	1	μA
I_{GSS}	gate-source leakage current	$V_{GS} = \pm 15\text{ V}$; $V_{DS} = 0$	–	–	± 10	nA
V_{GSth}	gate-source threshold voltage	$V_{GS} = V_{DS}$; $I_D = 1\text{ mA}$	0.8	–	2.4	V
R_{DSon}	drain-source on-state resistance	$V_{GS} = 2.6\text{ V}$; $I_D = 20\text{ mA}$	–	20	28	Ω
		$V_{GS} = 10\text{ V}$; $I_D = 150\text{ mA}$	–	14	–	Ω
$ y_{fs} $	transfer admittance	$V_{DS} = 15\text{ V}$; $I_D = 250\text{ mA}$	75	170	–	mS
C_{iss}	input capacitance	$V_{GS} = 0$; $V_{DS} = 10\text{ V}$; $f = 1\text{ MHz}$	–	50	65	pF
C_{oss}	output capacitance	$V_{GS} = 0$; $V_{DS} = 10\text{ V}$; $f = 1\text{ MHz}$	–	16	25	pF
C_{rss}	feedback capacitance	$V_{GS} = 0$; $V_{DS} = 10\text{ V}$; $f = 1\text{ MHz}$	–	4	10	pF
Switching times (see Figs 2 and 3)						
t_{on}	turn-on time	$V_{GS} = 0\text{ to }10\text{ V}$; $V_{DD} = 50\text{ V}$; $I_D = 250\text{ mA}$	–	2	10	ns
t_{off}	turn-off time	$V_{GS} = 0\text{ to }10\text{ V}$; $V_{DD} = 50\text{ V}$; $I_D = 200\text{ mA}$	–	5	20	ns

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PMBF107

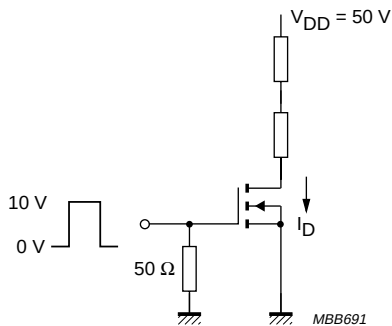


Fig.2 Switching time test circuit.

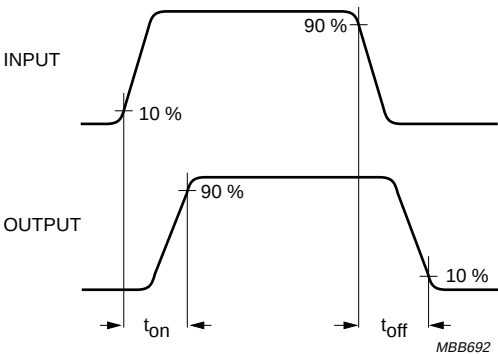


Fig.3 Input and output waveforms.

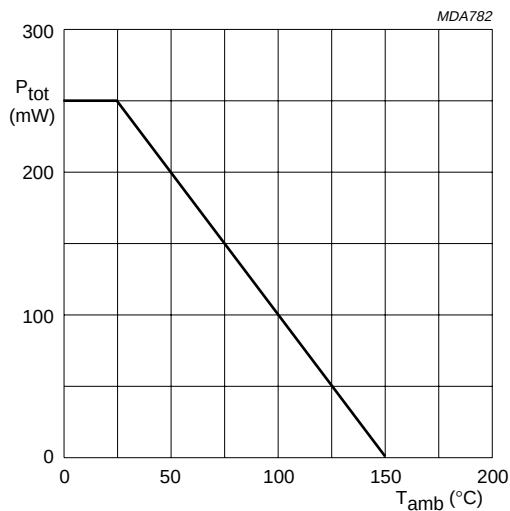


Fig.4 Power derating curve.

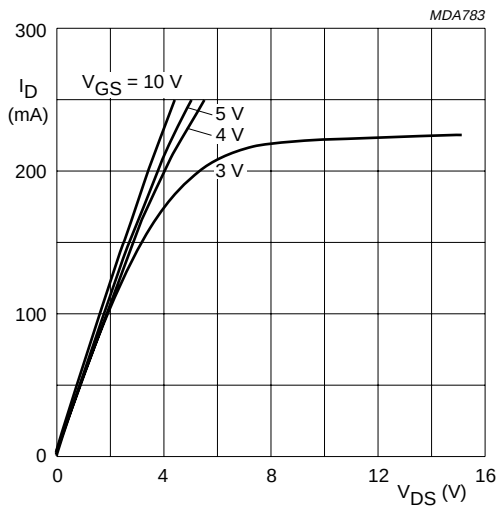


Fig.5 Typical output characteristics; $T_j = 25^\circ\text{C}$.

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PMBF107

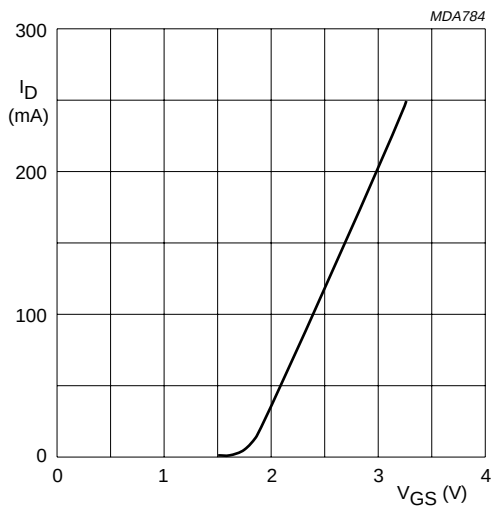


Fig.6 Typical transfer characteristic;
 $V_{DS} = 10$ V; $T_j = 25$ °C.

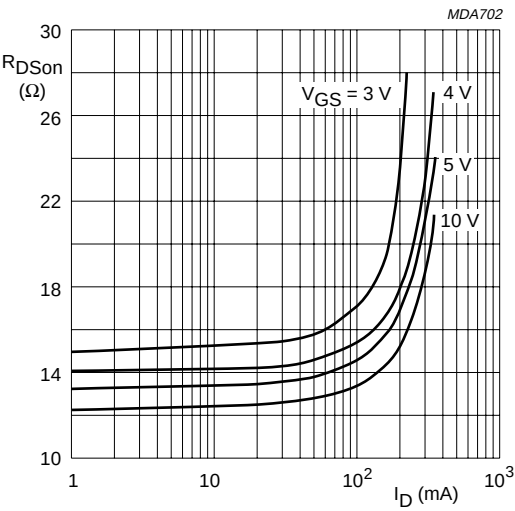


Fig.7 Typical on-resistance as a function of
drain current; $T_j = 25$ °C.

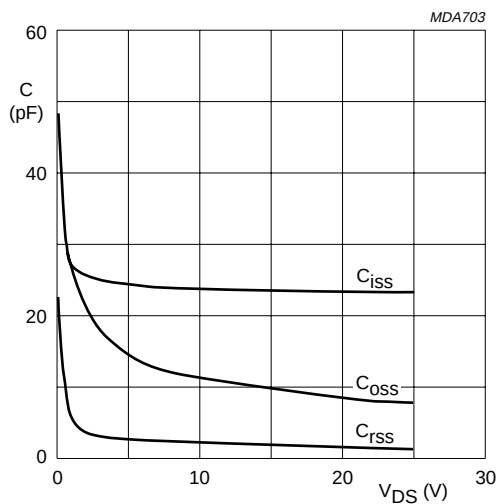


Fig.8 Typical capacitances as a function of
drain-source voltage; $V_{GS} = 0$; $f = 1$ MHz;
 $T_j = 25$ °C.

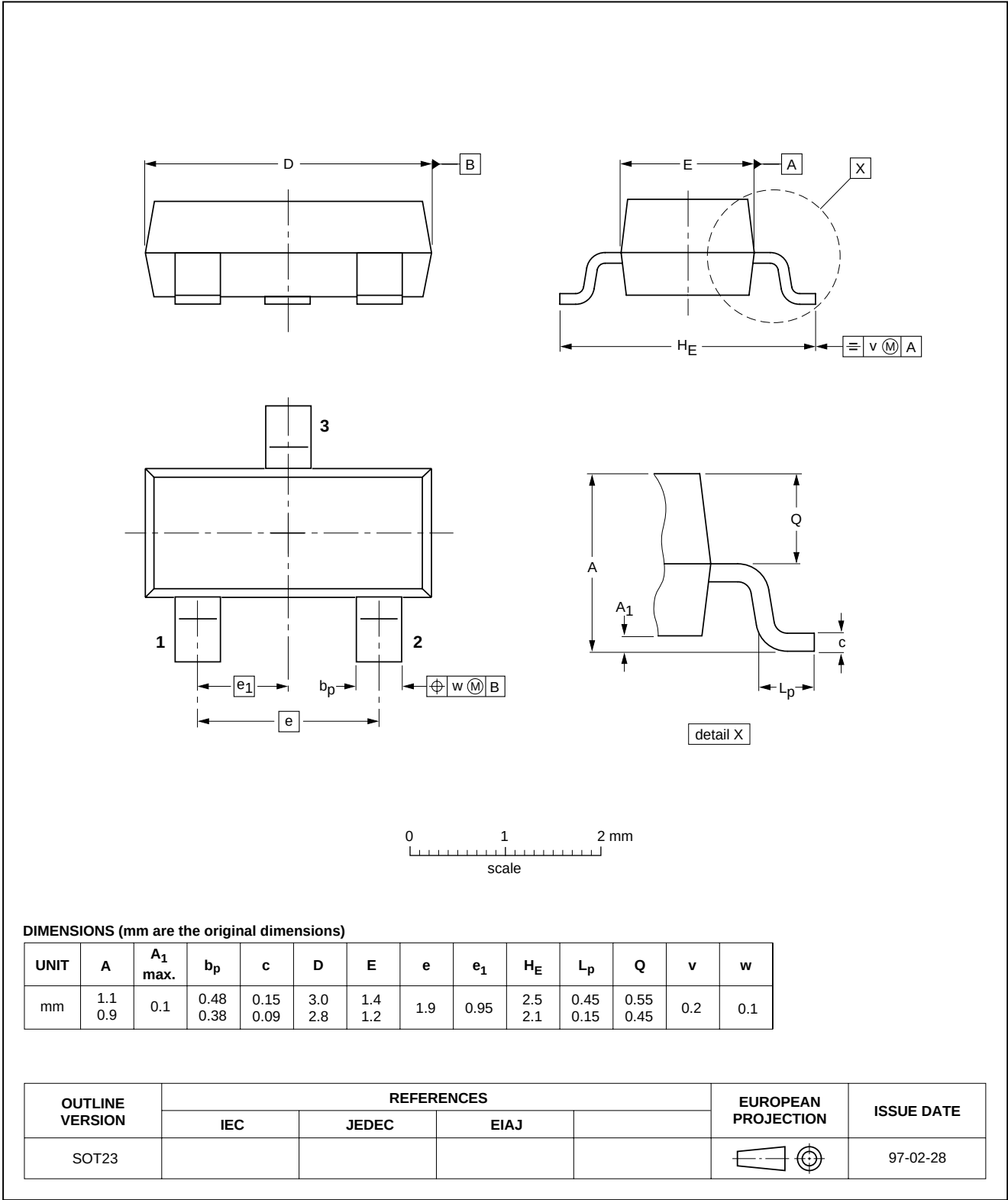
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PMBF107

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



**N-channel enhancement mode vertical
D-MOS transistor**

PMBF107**DEFINITIONS**

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Printed in The Netherlands

135108/00/03/pp8

Date of release: 1998 Mar 06

Document order number: 9397 750 03369

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